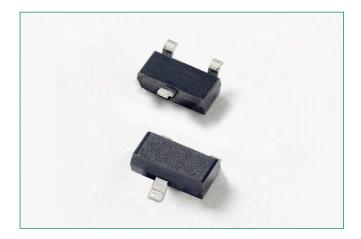
Thyristors Datasheet

SxX8BBS Series EV Series 0.8 Amp Sensitive SCRs

RoHS



Main Features

| Symbol | Value | Unit |
|---------------------------|-------|------|
| I _{T(RMS)} | 0.8 | А |
| $V_{\rm drm}/V_{\rm rrm}$ | 600 | V |
| Ι _{GT} | 200 | μΑ |

Description

This new sensitive SCR component series offers 600V $\mathrm{V}_{_{\mathrm{DRM}}}$ and 0.8A $I_{\text{T(RMS)}}$ capability in the smallest package size in the industry, SOT23. It is specifically designed for GFCI (Ground Fault Circuit Interrupter) applications. All SCRs junctions are glass-passivated to ensure long term reliability and parametric stability.

Features

- Very compact SOT23 SMT package
- Surge current capability up to 12A @ 60Hz
- Blocking voltage (V_{DRM} / V_{RRM}) capability - up to 600V
- High dv/dt noise immunity
- Improved turn-off time (t_a) <</p> 25 µsec
- Sensitive gate for direct microprocessor interface
- RoHS compliant and Halogen-Free

Applications

The SxX8BBS series is specifically designed for GFCI (Ground Fault Circuit Interrupter) and applications.

Schematic Symbol G $^{\circ}$ KO -OA

Pin out Anode 1 2 Cathode Gate

Absolute Maximum Ratings

| Symbol | Parameter | Value | Unit | | |
|---------------------------|--|--------------------------|------------------------|------------|------|
| $V_{\rm DSM}/V_{\rm RSM}$ | Peak non-repetitive blocking voltage | Pw=100µs | | 700 | V |
| I _{T(RMS)} | RMS on-state current (full sine wave) | | $T_c = 80^{\circ}C$ | 0.8 | А |
| I _{T(AV)} | Average on-state current | | $T_c = 80^{\circ}C$ | 0.51 | А |
| 1 | Non repetitive surge peak on-state current | | f= 50Hz | 10 | А |
| I _{TSM} | (Single cycle, T_j initial = 25°C) | | f= 60Hz | 12 | А |
| l ² t | I ² t Value for fusing | $t_p = 10 \text{ ms}$ | f= 50 Hz | 0.5 | A²s |
| 11 | i t value for fusing | $t_{p} = 8.3 \text{ ms}$ | f= 60 Hz | 0.6 | A²s |
| di/dt | Critical rate of rise of on-state current $\rm I_{g}$ = 10mA | 60 Hz | $T_{J} = 125^{\circ}C$ | 80 | A/µs |
| I _{GM} | Peak Gate Current | $t_p = 20 \ \mu s$ | $T_{J} = 125^{\circ}C$ | 1.0 | А |
| P _{G(AV)} | Average gate power dissipation | | $T_{J} = 125^{\circ}C$ | 0.1 | W |
| T _{stg} | Storage junction temperature range | | | -40 to 150 | °C |
| TJ | Operating junction temperature range | | | -40 to 125 | °C |



| Electrical Characteristics | (Т | _ | 25°C | unless | otherwise | specified) |
|-----------------------------------|----|-----|-------|--------|------------|------------|
| | 11 | _ = | ZO C, | uniess | other wise | specified) |

| Symbol | Description | Test Conditions | Limit | Value | Unit |
|------------------|---|--|-------|-------|------|
| 1 | DC Cata Trigger Current | \/6\/R100_O | MIN. | 50 | μA |
| I _{GT} | DC Gate Trigger Current | $V_{_{\mathrm{D}}}$ = 6V, $\mathrm{R}_{_{\mathrm{L}}}$ = 100 Ω | MAX. | 200 | μA |
| V _{GT} | DC Gate Trigger Voltage | $V_{_{ m D}}$ = 6V, $R_{_{ m L}}$ = 100 Ω | MAX. | 0.8 | V |
| V _{GRM} | Peak Reverse Gate Voltage | $I_{RG} = 10 \mu A$ | MIN. | 8 | V |
| I _H | Holding Current | Initial Current = 20mA | MAX. | 10 | mA |
| (dv/dt)s | Critical Rate-of-Rise of Off-State Voltage | $T_{J} = 125^{\circ}C$ $V_{D} = 67\%V_{DRM}/V_{RRM}$ Exp. Waveform, $R_{GK} = 1 k\Omega$ | MIN. | 50 | V/µs |
| V_{gD} | Gate Non-Trigger Voltage | | MIN. | 0.2 | V |
| t _q | Turn-Off Time | I _T =0.5A | MAX. | 25 | μs |
| t _{gt} | Turn-On Time | I _g =10mA,Pw= 15μsec, I _T = 1.6A(pk) | TYP. | 2.0 | μs |

Static Characteristics ($T_1 = 25^{\circ}$ C, unless otherwise specified)

| Symbol | Description | Test Conditions | Limit | Value | Unit |
|------------------------|-----------------------|------------------------|-------|-------|------|
| V _{TM} | Peak On-State Voltage | $I_{TM} = 1.6A (pk)$ | MAX. | 1.70 | V |
| 1 /1 | | $T_{J} = 25^{\circ}C$ | MAX. | 5 | μΑ |
| DRM ^{/ I} RRM | | $T_{J} = 125^{\circ}C$ | MAX. | 100 | μΑ |

Thermal Resistances

| Symbol | Description | Value | Unit |
|---------------------|-----------------------|-------|------|
| R _{e(JC)} | Junction to case (AC) | 45 | °C/W |
| R _{e(J-A)} | Junction to ambient | 220 | °C/W |



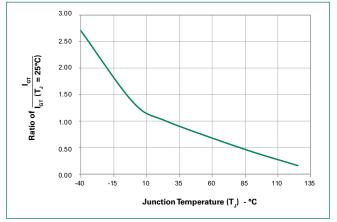
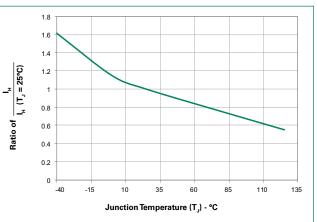


Figure 2: Normalized DC Holding Current vs. Junction Temperature



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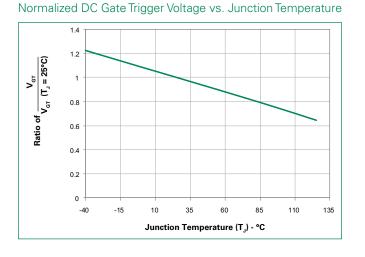


Figure 3:

Figure 4: On-State Current vs. On-State Voltage (Typical)

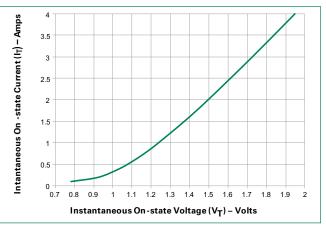


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

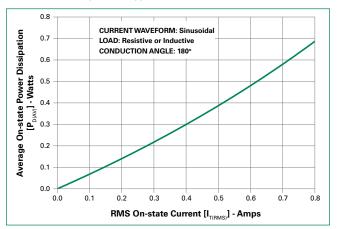
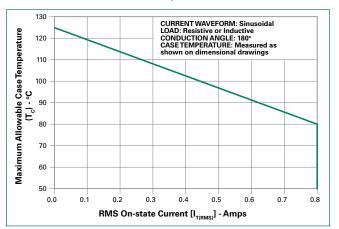
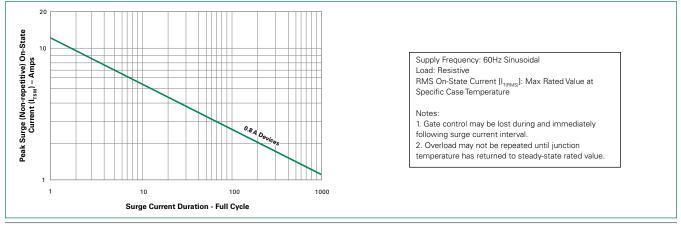


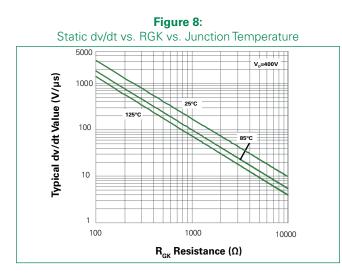
Figure 6: Maximum Allowable Case Temperature vs. On-State Current

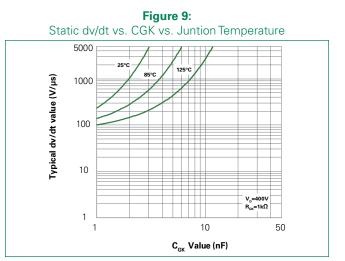






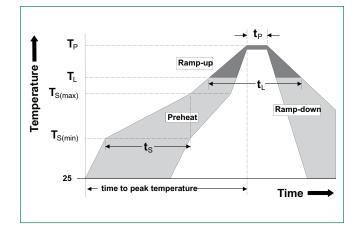
SxX8BBS Series EV Series 0.8 Amp Sensitive SCRs





Soldering Parameters

| Reflow Condition | | Pb – Free assembly |
|--|--|-------------------------|
| | - Temperature Min (T _{s(min)}) | 150°C |
| Pre Heat | - Temperature Max (T _{s(max)}) | 200°C |
| | - Time (min to max) (t _s) | 60 - 120 secs |
| Average ramp up rate (Liquidus Temp) (T_L) to peak | | 3°C/second max |
| $T_{S(max)}$ to T_L - F | Ramp-up Rate | 5°C/second max |
| Reflow | - Temperature (T _L) (Liquidus) | 217°C |
| nellow | - Time (min to max) (t _s) | 60 – 150 seconds |
| Peak Tempera | ature (T _P) | 260 ^{+0/-5} °C |
| Time within | 5°C of actual peak Temperature (t _p) | 30 seconds |
| Ramp-down Rate | | 6°C/second max |
| Time 25°C to peak Temperature (T _P) | | 8 minutes Max. |
| Do not excee | d | 260°C |



SxX8BBS Series EV Series 0.8 Amp Sensitive SCRs

Physical Specifications

| Terminal Finish | 100% Matte Tin-plated. |
|-----------------|---|
| Body Material | UL Recognized compound meeting flammability rating V-0. |
| Lead Material | Copper Alloy |

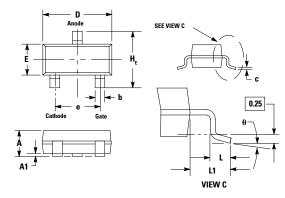
Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

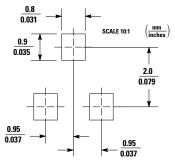
Reliability/Environmental Tests

| Test | Specifications and Conditions |
|-------------------------------|--|
| HTRB (AC Blocking) | MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ $\rm V_{\rm DRM}$ @ 125°C for 1008 hours |
| Temperature Cycling | MIL-STD-750, M-1051, 100 cycles; -55°C to +150°C; 15-min dwell-time |
| H3TRB | EIA / JEDEC, JESD22-A101 1008 hours; 160V - DC: 85°C; 85% rel humidity |
| UHAST | ESD22-A118, 96hours, 130°C, 85%RH |
| Resistance to Solder Heat | MIL-STD-750 Method 2031, 260°C, 10s |
| Solderability | ANSI/J-STD-002, category 3, Test A |
| Moisture Sensitivity Level | Level 1, JEDEC-J-STD-020D |

Dimensions – SOT-23



SOLDERING FOOTPRINT



| Dimensions | | Inches | | r | Villimeter | s |
|------------|------|--------|------|------|------------|------|
| Dimensions | Min | Тур | Max | Min | Тур | Max |
| Α | 0.04 | 0.04 | 0.04 | 0.89 | 1.02 | 1.12 |
| A1 | 0.00 | 0.00 | 0.01 | 0.01 | 0.10 | 0.15 |
| b | 0.02 | 0.02 | 0.02 | 0.38 | 0.46 | 0.51 |
| C | 0.00 | 0.01 | 0.01 | 0.08 | 0.13 | 0.18 |
| D | 0.11 | 0.11 | 0.12 | 2.80 | 2.90 | 3.04 |
| Е | 0.05 | 0.05 | 0.06 | 1.19 | 1.30 | 1.40 |
| е | 0.07 | 0.08 | 0.08 | 1.78 | 1.91 | 2.06 |
| L | 0.02 | 0.02 | 0.02 | 0.40 | 0.49 | 0.60 |
| L1 | 0.01 | 0.02 | 0.03 | 0.36 | 0.53 | 0.74 |
| н | 0.08 | 0.09 | 0.10 | 2.10 | 2.30 | 2.64 |
| θ | 0° | - | 10° | 0° | - | 10° |

Packing Options

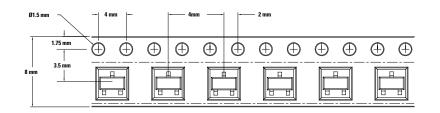
| Part Number | Marking | Weight | Packing Mode | Base Quantity |
|-------------|---------|--------|-----------------|------------------|
| S6X8BBSRP | 6X8 | 0.01g | Tape & Reel | 3000 |

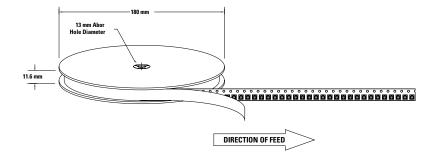
Product Selector

| Part Number | Voltage 600V | Gate Sensitivity | Package |
|-------------|-----------------|------------------|---------|
| S6X8BBS | Х | 200 µA | SOT-23 |

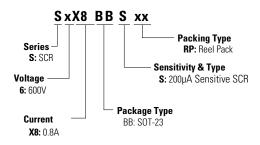


SOT-23 Reel Pack (RP) Specifications





Part Numbering System



Part Marking System



L: Location Code

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